

30V P-Channel MOSFET



SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

Key Parameter Performance

	Parameter		Value	Unit	
	V_{DS}		-30	V	
	R _{DS(on)} (max)	V _{GS} = -10V	95	mΩ	
ŀ		V _{GS} = -4.5V	140		
	Q_g		10	nC	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Load Switch
- PA Switch

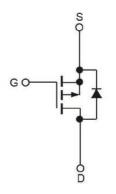
Ordering Information

Part No.	Package	Packing
TSM2307CX RFG	SOT-23	3kpcs / 7" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain

<900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

Block Diagram



P-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	Drain-Source Voltage		-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)		I _D	-3	Α	
Pulsed Drain Current (Note 2)		I _{DM}	-20	А	
Continuous Source Current (Diode Conduction)		I _S	-1.7	А	
Dawar Dissipation	T _a = 25°C	<u></u>	1.25	W	
Power Dissipation	T _a = 75°C	P _D	0.8		
Operating Junction Temperature		TJ	+150	°C	
Storage Temperature Range		T _{STG}	-50 to +150	°C	

<1000ppm antimony compounds







Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{ extsf{ hetaJC}}$	75	°C/W
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	130	°C/W

Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV _{DSS}	-30			V
Davis Os and Os Otata Basistan	$V_{GS} = -10V, I_D = -3A$			76	95	mΩ
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_D = -2A$	R _{DS(ON)}		103	140	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1		-3	V
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance (Note 4)	$V_{DS} = -10V, I_D = -6A$	g fs		5		S
Diode Forward Voltage	$I_S = -1.7V, V_{GS} = 0V$	V_{SD}			-1.2	V
Dynamic						
Total Gate Charge (Note 3,4)		Q_g		10	15	nC
Gate-Source Charge (Note 3,4)	$V_{DS} = -15V, I_D = -3A,$	Q_{gs}		1.9		
Gate-Drain Charge (Note 3,4)	$V_{GS} = -10V$	Q_{gd}		2		
Input Capacitance		C _{iss}		565		
Output Capacitance	$V_{DS} = -30V, V_{GS} = 0V,$	C _{oss}		126		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		75]
Switching			•	•		•
Turn-On Delay Time (Note 3,4))		t _{d(on)}		10	20	
Turn-On Rise Time (Note 3,4)	$V_{DD} = -15V, R_L = 15\Omega,$	t _r		9	20	
Turn-Off Delay Time (Note 3,4)	$I_D = -1A, V_{GEN} = -10V,$ $R_G = 6\Omega$	t _{d(off)}		27	50	ns
Turn-Off Fall Time (Note 3,4)	1/G -077	t _f		7	16	1

Note:

- 1.Limited by maximum junction temperature
- 2. Pulse width limited by safe operating area
- 3. Pulse test: pulse width ≤ 300µs, duty cycle ≤ 2%
- 4. Switching time is essentially independent of operating temperature.

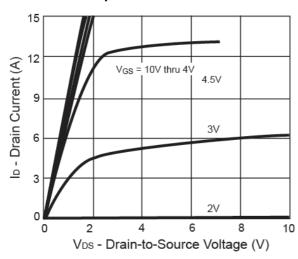


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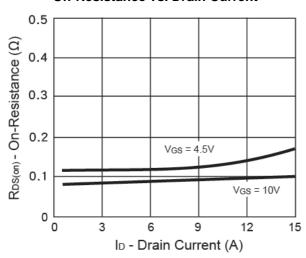


Electrical Characteristics Curve

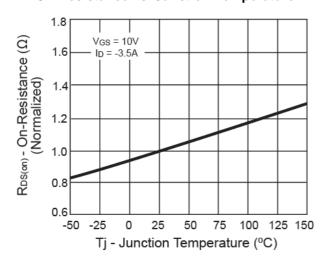
Output Characteristics



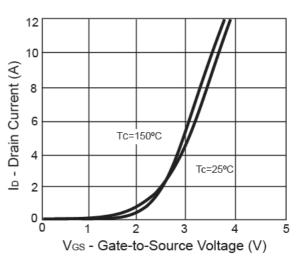
On-Resistance vs. Drain Current



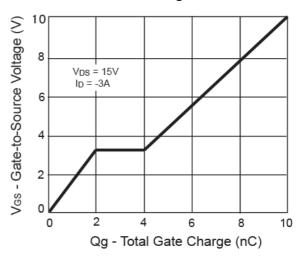
On-Resistance vs. Junction Temperature



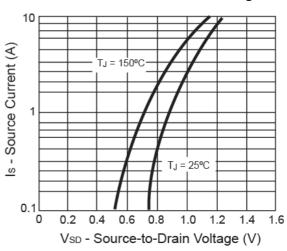
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



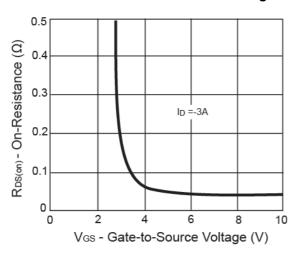


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Electrical Characteristics Curve

On-Resistance vs. Gate-Source Voltage



0.3 0.2 0.1 0.1 0.0 (a) Seo 0.2

25

50

Tj - Junction Temperature (°C)

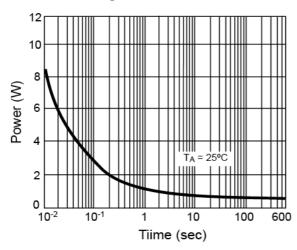
75

100

125 150

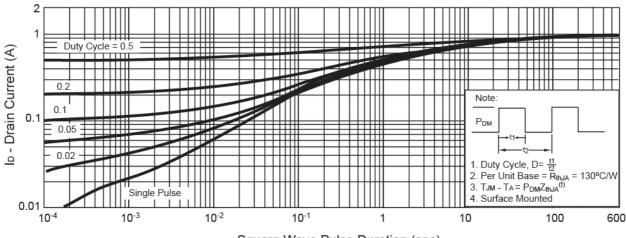
Threshold Voltage

Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

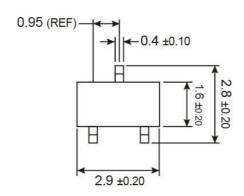
-0.3 -50 -25

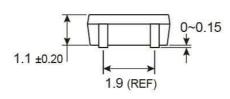


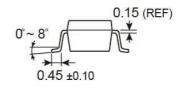
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SOT-23 Mechanical Drawing

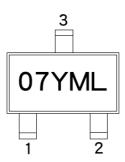






Unit: Millimeters

Marking Diagram



07 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



TSM2307CX 30V P-Channel MOSFET



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